Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection: 2 kV HBM
- Leadless ultra small SMD plastic package: 1.0 x 0.6 x 0.48 mm

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | 20 | V |
| V_{GS} | gate-source voltage | | | -8 | - | 8 | V |
| I _D | drain current | V _{GS} = 4.5 V; T _{amb} = 25 °C | [1] | - | - | 1.2 | Α |
| Static characteristics | | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 4.5 \text{ V}; I_D = 1.2 \text{ A}; T_j = 25 \text{ °C}$ | | - | 270 | 320 | mΩ |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--|----------------|
| 1 | G | gate | 1 | D I |
| 2 | S | source | 2 🔲 📗 3 | |
| 3 | D | drain | Transparent top view DFN1006-3 (SOT883) | G S 017aaa255 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | | |
|-------------|-----------|---|---------|--|--|--|--|
| | Name | Description | Version | | | | |
| PMZ290UNE2 | DFN1006-3 | DFN1006-3: leadless ultra small plastic package; 3 solder lands | SOT883 | | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMZ290UNE2 | SC |

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|--|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 20 | V |
| V_{GS} | gate-source voltage | | | -8 | 8 | V |
| I _D | drain current | V_{GS} = 4.5 V; T_{amb} = 25 °C | [1] | - | 1.2 | Α |
| | | V _{GS} = 4.5 V; T _{amb} = 100 °C | [1] | - | 0.8 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs | | - | 4 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 350 | mW |
| | | | [1] | - | 715 | mW |
| | | T _{sp} = 25 °C | | - | 5430 | mW |
| T _j | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain o | liode | | • | | | |
| Is | source current | T _{amb} = 25 °C | [1] | - | 0.7 | Α |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

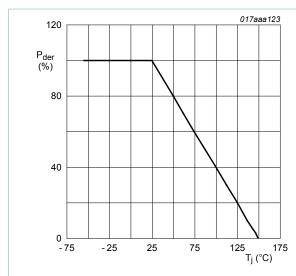


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

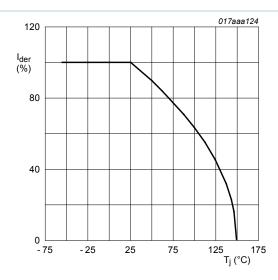


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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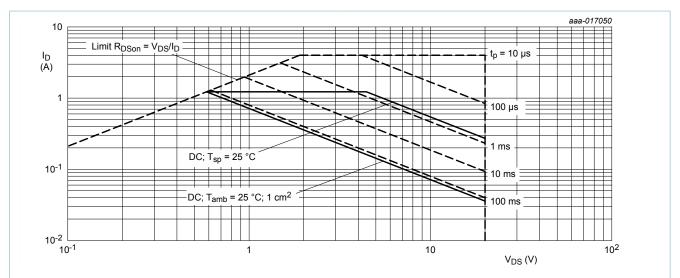


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--|--|------------|------------|-----|-----|-----|------|
| R _{th(j-a)} thermal resista from junction t ambient | thermal resistance | | [1] | - | 315 | 360 | K/W |
| | • | | <u>[2]</u> | - | 150 | 175 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 20 | 23 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

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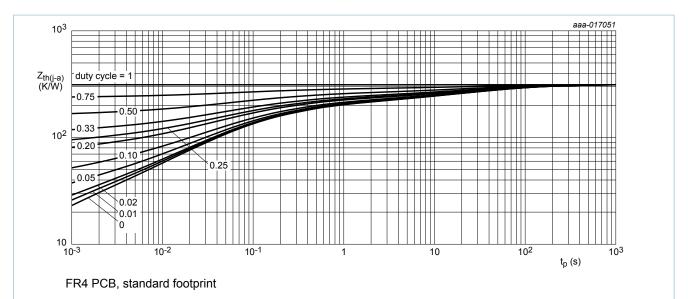
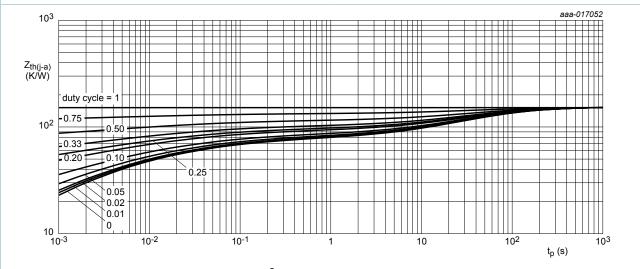


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain = 1 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|----------------------------------|---|------|-----|------|------|
| Static chara | acteristics | | ' | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C | 20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$ | 0.45 | 0.7 | 0.95 | V |
| I _{DSS} | drain leakage current | V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 5 | μA |
| | | V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -5 | μA |
| | | $V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | - | 1 | μA |
| | | V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -1 | μΑ |
| | | V_{GS} = 2.5 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| | | V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 4.5 V; I _D = 1.2 A; T _j = 25 °C | - | 270 | 320 | mΩ |
| | | V _{GS} = 4.5 V; I _D = 1.2 A; T _j = 150 °C | - | 400 | 475 | mΩ |
| | | V_{GS} = 2.5 V; I_D = 1.0 A; T_j = 25 °C | - | 360 | 480 | mΩ |
| | | V_{GS} = 1.8 V; I_D = 0.12 A; T_j = 25 °C | - | 470 | 680 | mΩ |
| | | V_{GS} = 1.5 V; I_D = 0.01 A; T_j = 25 °C | - | 600 | 1190 | mΩ |
| 9fs | forward transconductance | $V_{DS} = 10 \text{ V}; I_D = 1.23 \text{ A}; T_j = 25 \text{ °C}$ | - | 1.9 | - | S |
| Dynamic ch | naracteristics | | ' | ' | | |
| Q _{G(tot)} | total gate charge | $V_{DS} = 10 \text{ V}; I_D = 1.0 \text{ A}; V_{GS} = 4.5 \text{ V};$ | - | 0.8 | 1.4 | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 0.1 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.2 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V; | - | 46 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 9.6 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 7.7 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 10 V; I_{D} = 1.0 A; V_{GS} = 4.5 V; | - | 6 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$ | - | 10 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 11 | - | ns |
| t _f | fall time | | - | 4 | - | ns |
| Source-drai | in diode | | I | 1 | 1 | 1 |
| V_{SD} | source-drain voltage | $I_S = 0.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 0.9 | 1.2 | V |
| | | | 1 | 1 | | |

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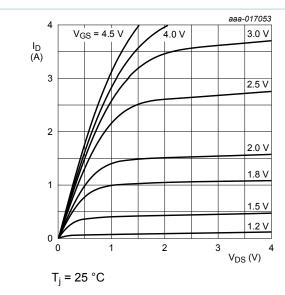
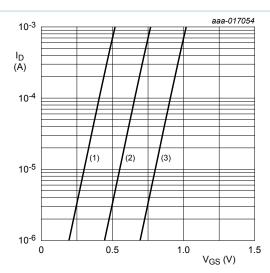


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $V_{DS} = 5 V$

T_i = 25 °C

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

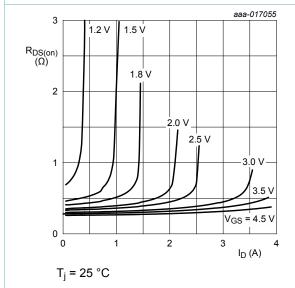


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

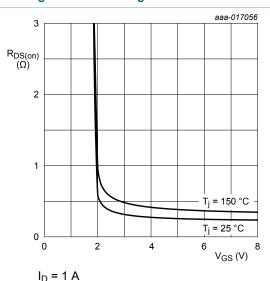


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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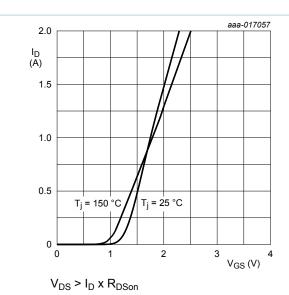


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

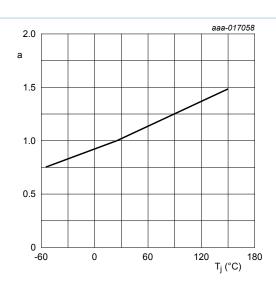
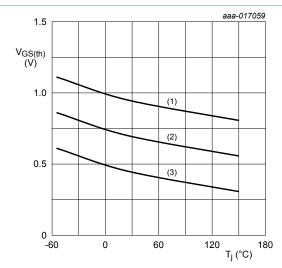


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

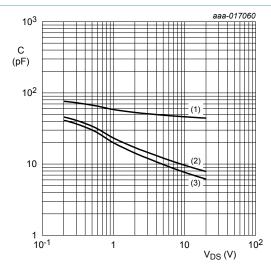
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 250 \mu A; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of ambient temperature

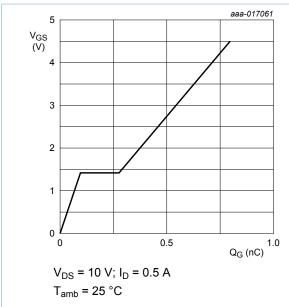


 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_G(tot)
003aaa508

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

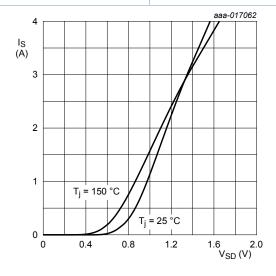
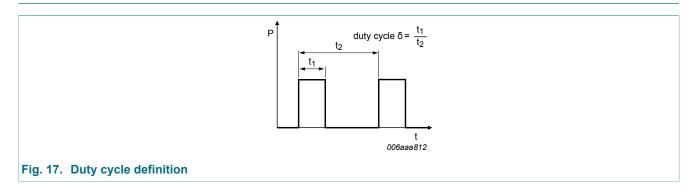


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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11. Test information



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12. Package outline

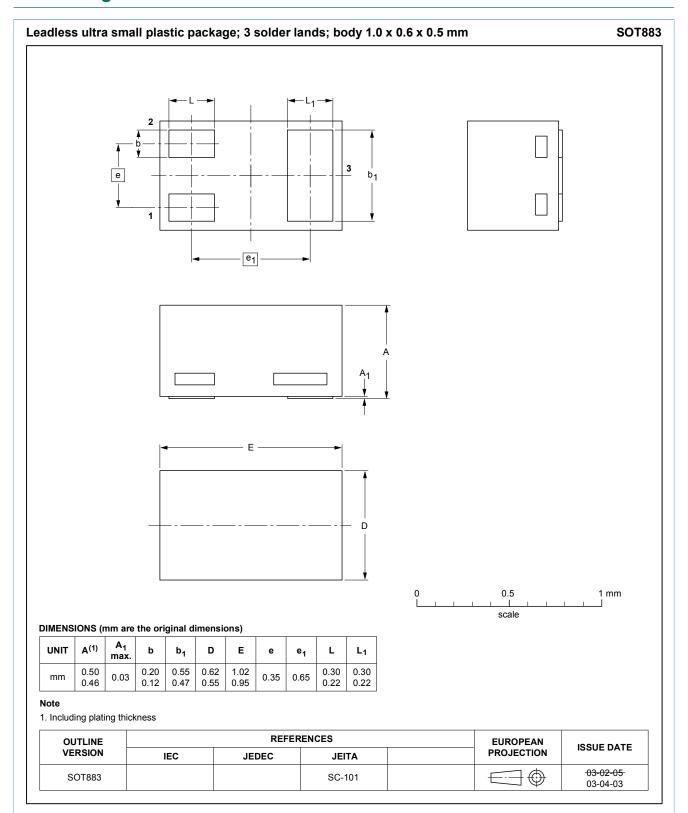


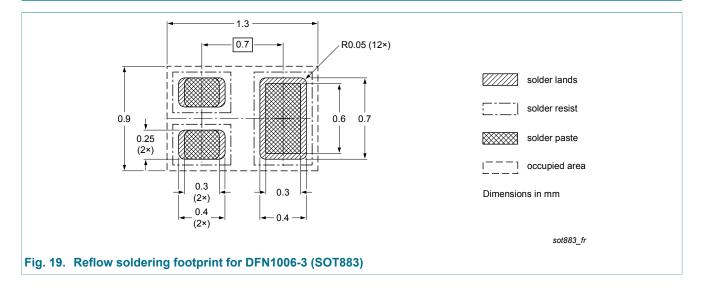
Fig. 18. Package outline DFN1006-3 (SOT883)

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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PMZ290UNE2 v.1 | 20150324 | Product data sheet | - | - |

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15. Legal information

15.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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| Product [short] data sheet | Production | This document contains the product specification. |

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